

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

545 papers	17,361 citations	63 h-index	112 g-index
583 ext. papers	19,353 ext. citations	3.3 avg, IF	6.69 L-index

#	Paper	IF	Citations
545	GaN: Processing, defects, and devices. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 1-78	2.5	1469
544	A review of Ga <sub>2</sub> O <sub>3</sub> materials, processing, and devices. <i>Applied Physics Reviews</i> , <b>2018</b> , 5, 011301	17.3	1114
543	Hydrogen-selective sensing at room temperature with ZnO nanorods. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 243503	3.4	475
542	Fabrication and performance of GaN electronic devices. <i>Materials Science and Engineering Reports</i> , <b>2000</b> , 30, 55-212	30.9	373
541	Magnetic properties of n-GaMnN thin films. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3964-3966	3.4	310
540	Perspective Opportunities and Future Directions for Ga <sub>2</sub> O <sub>3</sub> . <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, P356-P359	2	261
539	Perspective: Ga <sub>2</sub> O <sub>3</sub> for ultra-high power rectifiers and MOSFETS. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 220901	2.5	245
538	Hydrogen sensing at room temperature with Pt-coated ZnO thin films and nanorods. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 222106	3.4	244
537	Recent advances in wide bandgap semiconductor biological and gas sensors. <i>Progress in Materials Science</i> , <b>2010</b> , 55, 1-59	42.2	212
536	Depletion-mode ZnO nanowire field-effect transistor. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2274-2276	3.4	208
535	Effect of temperature on Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> )/GaN metaloxide semiconductor field-effect transistors. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 3893-3895	3.4	199
534	Hydrogen incorporation and diffusivity in plasma-exposed bulk ZnO. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 385-387	3.4	186
533	GaN Electronics. <i>Advanced Materials</i> , <b>2000</b> , 12, 1571-1580	24	186
532	Review Ionizing Radiation Damage Effects on GaN Devices. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q35-Q60	2	182
531	The control of cell adhesion and viability by zinc oxide nanorods. <i>Biomaterials</i> , <b>2008</b> , 29, 3743-3749	15.6	166
530	A Review of Dry Etching of GaN and Related Materials. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>2000</b> , 5, 1		148
529	Review of radiation damage in GaN-based materials and devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2013</b> , 31, 050801	2.9	145

528	Radiation effects in GaN materials and devices. <i>Journal of Materials Chemistry C</i> , <b>2013</b> , 1, 877-887	7.1	139
527	Electrical transport properties of single ZnO nanorods. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2002-2004	3.4	138
526	Demonstration of enhancement-mode p- and n-channel GaAs MOSFETS with Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) As gate oxide. <i>Solid-State Electronics</i> , <b>1997</b> , 41, 1751-1753	1.7	135
525	ZnO spintronics and nanowire devices. <i>Journal of Electronic Materials</i> , <b>2006</b> , 35, 862-868	1.9	131
524	pH measurements with single ZnO nanorods integrated with a microchannel. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 112105	3.4	127
523	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2017</b> , 110, 192101	3.4	118
522	Pt/ZnO nanowire Schottky diodes. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3107-3109	3.4	116
521	Low bias electron cyclotron resonance plasma etching of GaN, AlN, and InN. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 2294-2296	3.4	116
520	2300V Reverse Breakdown Voltage Ga <sub>2</sub> O <sub>3</sub> Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , <b>2018</b> , 7, Q92-Q96	2	116
519	High Breakdown Voltage (001) $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Schottky Rectifiers. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 906-909	4.4	114
518	Electrical detection of biomaterials using AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 031101	2.5	101
517	High performance indium gallium zinc oxide thin film transistors fabricated on polyethylene terephthalate substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 082102	3.4	101
516	UV photoresponse of single ZnO nanowires. <i>Applied Physics A: Materials Science and Processing</i> , <b>2005</b> , 80, 497-499	2.6	98
515	Pressure-induced changes in the conductivity of AlGa <sub>N</sub> /Ga <sub>N</sub> high-electron mobility-transistor membranes. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2962-2964	3.4	97
514	Oxygen sensors made by monolayer graphene under room temperature. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 243502	3.4	96
513	Functionalizing Zn- and O-terminated ZnO with thiols. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 104514	2.5	93
512	MgO/p-GaN enhancement mode metal-oxide semiconductor field-effect transistors. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2919-2921	3.4	93
511	Hydrogen and ozone gas sensing using multiple ZnO nanorods. <i>Applied Physics A: Materials Science and Processing</i> , <b>2005</b> , 80, 1029-1032	2.6	91

- 510 Radiation damage effects in Ga<sub>2</sub>O<sub>3</sub> materials and devices. *Journal of Materials Chemistry C*, **2019**, 7, 10-24. 90
- 509 Quasi-two-dimensional Gallium oxide solar-blind photodetectors with ultrahigh responsivity. *Journal of Materials Chemistry C*, **2016**, 4, 9245-9250. 7.1 89
- 508 Gd<sub>2</sub>O<sub>3</sub>/GaN metal-oxide-semiconductor field-effect transistor. *Applied Physics Letters*, **2000**, 77, 3230-3232. 3.4 89
- 507 Lateral Al<sub>x</sub>Ga<sub>1-x</sub>N power rectifiers with 9.7 kV reverse breakdown voltage. *Applied Physics Letters*, **2001**, 78, 823-825. 3.4 85
- 506 Room temperature hydrogen detection using Pd-coated GaN nanowires. *Applied Physics Letters*, **2008**, 93, 072109. 3.4 84
- 505 Zn<sub>0.9</sub>Mg<sub>0.1</sub>O/ZnO p-n junctions grown by pulsed-laser deposition. *Applied Physics Letters*, **2004**, 85, 1169-1171. 3.4 81
- 504 Phosphorus doped ZnO light emitting diodes fabricated via pulsed laser deposition. *Applied Physics Letters*, **2008**, 92, 112108. 3.4 80
- 503 Electrical detection of deoxyribonucleic acid hybridization with AlGa<sub>0.4</sub>N/GaN high electron mobility transistors. *Applied Physics Letters*, **2006**, 89, 122102. 3.4 80
- 502 Prostate specific antigen detection using AlGa<sub>0.4</sub>N/GaN high electron mobility transistors. *Applied Physics Letters*, **2007**, 91, 112106. 3.4 80
- 501 AlGa<sub>0.4</sub>N/GaN-based metal-oxide-semiconductor diode-based hydrogen gas sensor. *Applied Physics Letters*, **2004**, 84, 1123-1125. 3.4 80
- 500 Effect of front and back gates on Ga<sub>2</sub>O<sub>3</sub> nano-belt field-effect transistors. *Applied Physics Letters*, **2016**, 109, 062102. 3.4 79
- 499 Wide Bandgap Semiconductor One-Dimensional Nanostructures for Applications in Nanoelectronics and Nanosensors. *Nanomaterials and Nanotechnology*, **2013**, 3, 1. 2.9 78
- 498 High mobility InGaZnO<sub>4</sub> thin-film transistors on paper. *Applied Physics Letters*, **2009**, 94, 072103. 3.4 78
- 497 Temperature-dependent characteristics of Pt Schottky contacts on n-type ZnO. *Applied Physics Letters*, **2004**, 84, 2835-2837. 3.4 77
- 496 Influence of High-Energy Proton Irradiation on GaO Nanobelt Field-Effect Transistors. *ACS Applied Materials & Interfaces*, **2017**, 9, 40471-40476. 9.5 76
- 495 Breakdown voltage and reverse recovery characteristics of free-standing GaN Schottky rectifiers. *IEEE Transactions on Electron Devices*, **2002**, 49, 32-36. 2.9 76
- 494 Gadolinium Oxide and Scandium Oxide: Gate Dielectrics for GaN MOSFETs. *Physica Status Solidi A*, **2001**, 188, 239-242. 74
- 493 Point defect induced degradation of electrical properties of Ga<sub>2</sub>O<sub>3</sub> by 10 MeV proton damage. *Applied Physics Letters*, **2018**, 112, 032107. 3.4 72

492	Inductively coupled plasma-induced etch damage of GaN p-n junctions. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2000</b> , 18, 1139-1143	2.9	71
491	Low-voltage indium gallium zinc oxide thin film transistors on paper substrates. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 053510	3.4	68
490	Synthesis and microstructure of vertically aligned ZnO nanowires grown by high-pressure-assisted pulsed-laser deposition. <i>Journal of Materials Science</i> , <b>2008</b> , 43, 6925-6932	4.3	68
489	Detection of hydrogen at room temperature with catalyst-coated multiple ZnO nanorods. <i>Applied Physics A: Materials Science and Processing</i> , <b>2005</b> , 81, 1117-1119	2.6	68
488	Carrier concentration dependence of Ti/Al/Pt/Au contact resistance on n-type ZnO. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 544-546	3.4	67
487	Influence of $^{60}\text{Co}$ rays on dc performance of AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 604-606	3.4	67
486	High voltage GaN Schottky rectifiers. <i>IEEE Transactions on Electron Devices</i> , <b>2000</b> , 47, 692-696	2.9	67
485	300°C GaN/AlGaIn Heterojunction Bipolar Transistor. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1998</b> , 3, 1		66
484	. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 407-411	2.9	64
483	Temperature-Dependent Characteristics of Ni/Au and Pt/Au Schottky Diodes on $\text{InGa}_2\text{O}_3$ . <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, P68-P72	2	63
482	Comparison of MOS and Schottky W/Pt/GaN diodes for hydrogen detection. <i>Sensors and Actuators B: Chemical</i> , <b>2005</b> , 104, 232-236	8.5	63
481	Electrical transport properties of single GaN and InN nanowires. <i>Journal of Electronic Materials</i> , <b>2006</b> , 35, 738-743	1.9	60
480	Transport properties of InN nanowires. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 093112	3.4	60
479	Improved Pt/Au and W/Pt/Au Schottky contacts on n-type ZnO using ozone cleaning. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 5133-5135	3.4	60
478	Electrical properties of bulk semi-insulating $\text{InGa}_2\text{O}_3$ (Fe). <i>Applied Physics Letters</i> , <b>2018</b> , 113, 142102	3.4	59
477	GaN n- and p-type Schottky diodes: Effect of dry etch damage. <i>IEEE Transactions on Electron Devices</i> , <b>2000</b> , 47, 1320-1324	2.9	58
476	Energy band offsets of dielectrics on $\text{InGaZnO}_4$ . <i>Applied Physics Reviews</i> , <b>2017</b> , 4, 021301	17.3	57
475	Tuning the thickness of exfoliated quasi-two-dimensional $\text{InGa}_2\text{O}_3$ flakes by plasma etching. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 131901	3.4	54

474	REVIEW OF RECENT ADVANCES IN TRANSITION AND LANTHANIDE METALDOPED GaN AND ZnO. <i>Chemical Engineering Communications</i> , <b>2009</b> , 196, 1030-1053	2.2	53
473	Vertical and lateral GaN rectifiers on free-standing GaN substrates. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 1555-1557	3.4	53
472	Measurement of Zn <sub>0.95</sub> Cd <sub>0.05</sub> O/ZnO (0001) heterojunction band offsets by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 192106	3.4	52
471	Pt-coated InN nanorods for selective detection of hydrogen at room temperature. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 1891		52
470	Inductively coupled plasma etching of bulk 6H-SiC and thin-film SiCN in NF <sub>3</sub> chemistries. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1998</b> , 16, 2204-2209	2.9	52
469	Ga <sub>2</sub> O <sub>3</sub> Schottky rectifiers with 1 ampere forward current, 650 V reverse breakdown and 26.5 MW.cm <sup>-2</sup> figure-of-merit. <i>AIP Advances</i> , <b>2018</b> , 8, 055026	1.5	51
468	Improved Ni based composite Ohmic contact to n-SiC for high temperature and high power device applications. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 2652-2657	2.5	51
467	Hole traps and persistent photocapacitance in proton irradiated EGa <sub>2</sub> O <sub>3</sub> films doped with Si. <i>APL Materials</i> , <b>2018</b> , 6, 096102	5.7	50
466	c-erbB-2 sensing using AlGaIn/GaN high electron mobility transistors for breast cancer detection. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 192103	3.4	49
465	Improved hydrogen detection sensitivity in N-polar GaN Schottky diodes. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 212108	3.4	48
464	ZnO and Related Materials for Sensors and Light-Emitting Diodes. <i>Journal of Electronic Materials</i> , <b>2008</b> , 37, 1426-1432	1.9	48
463	Comparison of gate and drain current detection of hydrogen at room temperature with AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 172105	3.4	48
462	Band alignment of Al <sub>2</sub> O <sub>3</sub> with (001) EGa <sub>2</sub> O <sub>3</sub> . <i>Vacuum</i> , <b>2017</b> , 142, 52-57	3.7	47
461	Effect of 5 MeV proton irradiation damage on performance of EGa <sub>2</sub> O <sub>3</sub> photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 041213	1.3	47
460	Randomized clinical study of wear of enamel antagonists against polished monolithic zirconia crowns. <i>Journal of Dentistry</i> , <b>2018</b> , 68, 19-27	4.8	46
459	Comparison of dry etch chemistries for SiC. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1997</b> , 15, 885-889	2.9	46
458	Enzyme-based lactic acid detection using AlGaIn/GaN high electron mobility transistors with ZnO nanorods grown on the gate region. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 042114	3.4	46
457	Determination of MgO/GaN heterojunction band offsets by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 042113	3.4	46

456	Novel insulators for gate dielectrics and surface passivation of GaN-based electronic devices. <i>Materials Science and Engineering Reports</i> , <b>2004</b> , 44, 151-184	30.9	46
455	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated $\text{AlGa}_2\text{O}_3$ . <i>Applied Physics Letters</i> , <b>2018</b> , 113, 092102	3.4	46
454	Low Hg(II) ion concentration electrical detection with AlGaIn/GaN high electron mobility transistors. <i>Sensors and Actuators B: Chemical</i> , <b>2008</b> , 134, 386-389	8.5	45
453	Contacts to p-type ZnMgO. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1904-1906	3.4	45
452	Al composition dependence of breakdown voltage in $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Schottky rectifiers. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1767-1769	3.4	45
451	Ultradeep, low-damage dry etching of SiC. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 739-741	3.4	45
450	Gamma irradiation impact on electronic carrier transport in AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 062102	3.4	44
449	Isolation blocking voltage of nitrogen ion-implanted AlGaIn/GaN high electron mobility transistor structure. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 262116	3.4	43
448	Development of enhancement mode AlN/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 263505	3.4	43
447	Wireless hydrogen sensor network using AlGaIn/GaN high electron mobility transistor differential diode sensors. <i>Sensors and Actuators B: Chemical</i> , <b>2008</b> , 135, 188-194	8.5	43
446	Electrical detection of kidney injury molecule-1 with AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 222101	3.4	43
445	Robust detection of hydrogen using differential AlGaIn/GaN high electron mobility transistor sensing diodes. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 242111	3.4	42
444	Effects of $\text{Sc}_2\text{O}_3$ and MgO passivation layers on the output power of AlGaIn/GaN HEMTs. <i>IEEE Electron Device Letters</i> , <b>2002</b> , 23, 505-507	4.4	42
443	1.5 MeV electron irradiation damage in $\text{AlGa}_2\text{O}_3$ vertical rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2017</b> , 35, 031208	1.3	41
442	Toward conductive traces: Dip Pen Nanolithography of silver nanoparticle-based inks. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 143105	3.4	41
441	High-energy proton irradiation effects on AlGaIn/GaN high-electron mobility transistors. <i>Journal of Electronic Materials</i> , <b>2002</b> , 31, 437-441	1.9	41
440	Optical and electrical properties of GaMnN films grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 4989-4993	2.5	41
439	$\text{CO}_2$ detection using polyethylenimine/starch functionalized AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 232102	3.4	39



- 438 Low-temperature-fabricated InGaZnO<sub>4</sub> thin film transistors on polyimide clean-room tape. *Applied Physics Letters*, **2008**, 93, 252103 3-4 38
- 437 Band-edge electroluminescence from N<sup>+</sup>-implanted bulk ZnO. *Applied Physics Letters*, **2006**, 88, 102107 3-4 38
- 436 Ti/Au n-type Ohmic contacts to bulk ZnO substrates. *Applied Physics Letters*, **2005**, 87, 212106 3-4 38
- 435 Sensitivity of Pt/ZnO Schottky diode characteristics to hydrogen. *Applied Physics Letters*, **2004**, 84, 1698-1700 3-4 38
- 434 Inductively coupled plasma etch damage in (-201) Ga<sub>2</sub>O<sub>3</sub> Schottky diodes. *Applied Physics Letters*, **2017**, 110, 142101 3-4 37
- 433 Effect of 1.5 MeV electron irradiation on E<sub>g</sub>Ga<sub>2</sub>O<sub>3</sub> carrier lifetime and diffusion length. *Applied Physics Letters*, **2018**, 112, 082104 3-4 37
- 432 Diffusion length of non-equilibrium minority charge carriers in E<sub>g</sub>Ga<sub>2</sub>O<sub>3</sub> measured by electron beam induced current. *Journal of Applied Physics*, **2018**, 123, 185704 2-5 37
- 431 Growth and Characterization of GaN Nanowires for Hydrogen Sensors. *Journal of Electronic Materials*, **2009**, 38, 490-494 1-9 37
- 430 Capacitance pressure sensor based on GaN high-electron-mobility transistor-on-Si membrane. *Applied Physics Letters*, **2005**, 86, 253502 3-4 37
- 429 Design of edge termination for GaN power Schottky diodes. *Journal of Electronic Materials*, **2005**, 34, 370-374 1-9 36
- 428 InGaAsN/AlGaAs P-n-p heterojunction bipolar transistor. *Applied Physics Letters*, **2000**, 76, 2788-2790 3-4 36
- 427 Temperature dependence and current transport mechanisms in Al<sub>x</sub>Ga<sub>1-x</sub>N Schottky rectifiers. *Applied Physics Letters*, **2000**, 76, 3816-3818 3-4 36
- 426 Band offsets in ITO/Ga<sub>2</sub>O<sub>3</sub> heterostructures. *Applied Surface Science*, **2017**, 422, 179-183 6-7 35
- 425 A comparative study of wet etching and contacts on (2001) and (010) oriented E<sub>g</sub>Ga<sub>2</sub>O<sub>3</sub>. *Journal of Alloys and Compounds*, **2018**, 731, 118-125 5-7 35
- 424 Annealing of dry etch damage in metallized and bare (-201) Ga<sub>2</sub>O<sub>3</sub>. *Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics*, **2017**, 35, 051201 1-3 35
- 423 Measurement of SiO<sub>2</sub>/InZnGaO<sub>4</sub> heterojunction band offsets by x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2011**, 98, 242110 3-4 35
- 422 Dielectric passivation effects on ZnO light emitting diodes. *Applied Physics Letters*, **2008**, 92, 112101 3-4 35
- 421 Thermal degradation of electrical properties and morphology of bulk single-crystal ZnO surfaces. *Applied Physics Letters*, **2004**, 85, 3468-3470 3-4 35



420	Botulinum toxin detection using AlGaNGaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 262101	3.4	34
419	Wireless Detection System for Glucose and pH Sensing in Exhaled Breath Condensate Using AlGaNGaN High Electron Mobility Transistors. <i>IEEE Sensors Journal</i> , <b>2010</b> , 10, 64-70	4	33
418	Electric-Field-Driven Degradation in off-State Step-Stressed AlGaNGaN High-Electron Mobility Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2011</b> , 11, 187-193	1.6	33
417	Ohmic contacts on n-type EGa2O3 using AZO/Ti/Au. <i>AIP Advances</i> , <b>2017</b> , 7, 095313	1.5	32
416	Improved morphology for ohmic contacts to AlGaNGaN high electron mobility transistors using WSix- or W-based metallization. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3910-3912	3.4	32
415	Contact resistivity and transport mechanisms in W contacts to p- and n-GaN. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 2048-2053	2.5	32
414	Selective-hydrogen sensing at room temperature with Pt-coated InN nanobelts. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 202109	3.4	31
413	Characterization of bulk GaN rectifiers for hydrogen gas sensing. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 2373		31
412	High dose Co-60 gamma irradiation of InGaN quantum well light-emitting diodes. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 212107	3.4	31
411	Vertical Geometry, 2-A Forward Current Ga2O3 Schottky Rectifiers on Bulk Ga2O3 Substrates. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 2790-2796	2.9	30
410	Effect of humidity on hydrogen sensitivity of Pt-gated AlGaNGaN high electron mobility transistor based sensors. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 232106	3.4	30
409	Characterization of the gate oxide of an AlGaNGaN high electron mobility transistor. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 122103	3.4	30
408	Carrier concentration dependence of Ti/Au specific contact resistance on n-type amorphous indium zinc oxide thin films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 122102	3.4	30
407	Detection of halide ions with AlGaNGaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 173502	3.4	30
406	Plasma damage in p-GaN. <i>Journal of Electronic Materials</i> , <b>2000</b> , 29, 256-261	1.9	30
405	Effect of surface treatments on electrical properties of EGa2O3. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2018</b> , 36, 061201	1.3	30
404	Valence and conduction band offsets in AZO/Ga2O3 heterostructures. <i>Vacuum</i> , <b>2017</b> , 141, 103-108	3.7	29
403	Hydrogen plasma treatment of EGa2O3: Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 032101	3.4	29

402	Highly sensitive AlGaIn/GaN diode-based hydrogen sensors using platinum nanonetworks. <i>Sensors and Actuators B: Chemical</i> , <b>2012</b> , 164, 64-68	8.5	29
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